M66258FP

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8192 x 8-BIT LINE MEMORY

DESCRIPTION

The M66258FP is high speed line memory that uses high performance silicon gate CMOS process technology and adopts the FIFO (First In First Out) structure consisting of 8192 words x 8 bits.

The M66258FP, performing reading and writing operations at different cycles independently and asynchronously, is optimal for buffer memory to be used between equipment of different data processing speeds.

FEATURES

- · Memory configuration 8192 words x 8 bits configuration
- · High speed cycle 20 ns (Min.)
- High speed access 16 ns (Max.)
- · Output hold

3 ns (Min.)

- · Reading and writing operations can be completely carried out independently and asynchronously.
- Variable length delay bit
- TTL direct connection allowable Input/output 3 states
- Output

APPLICATION

• Digital copying machine, laser beam printer, high speed facsimile, etc.

FUNCTIONAL DESCRIPTION

When write enable input $\overline{\text{WE}}$ is set to "L", the contents of data inputs D0 to D7 are read in synchronization with a rising edge of write lock input WCK to perform writing operation. When this is the case, the write address counter is also incremented simultaneously. When \overline{WE} is set to "H", the writing operation is inhibited and the write address counter stops.

When write reset input WRES is set to "L", the write address counter is initialized.

When read enable input \overline{RE} is set to "L", the contents of memory are output to data outputs Q0 to Q7 in synchronization with a rising edge of read clock input RCK to perform reading operation. When this is the case, the read address counter is incremented simultaneously.

When RE is set to "H", the reading operation is inhibited and the read address counter stops. The outputs are placed in a high impedance state.

When read reset input RRES is set to "L", the read address counter is initialized.





ABSOLUTE MAXIMUM RATINGS (Ta=0 - 70 °C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
Vcc	Supply voltage		-0.5 - +6.0	V
Vi	Input voltage	Value based on the GND pin	-0.5 – Vcc+0.5	V
Vo	Output voltage		-0.5 - Vcc+0.5	V
Pd	Power dispersion	Ta=25 °C	825	mW
Tstg	Storage temperature		-65 — 150	°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Linit		
		Min.	Тур.	Max.	Unit
Vcc	Supply voltage	4.5	5.0	5.5	V
GND	Supply voltage		0		V
Topr	Operating temperature	0 - 70		°C	

ELECTRICAL CHARACTERISTICS (Ta=0 - 70 °C, Vcc=5V±10%, GND=0V unless otherwise noted)

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Symbol	nbol Parameter Conditions		ditions	Min.	Тур.	Max.	Unit
Vih	High-level input voltage			2.0			V
VIL	Low-level input voltage					0.8	V
Vон	High-level output voltage	Iон = -4mA		Vcc-0.8			V
Vol	Low-level output voltage	IOL = 4mA				0.55	V
Ін	High-level input current	VI = VCC	WE, WRES, WCK, RE, RRES, RCK, D0 – D7			1.0	μA
lı.	Low-level input current	VI = GND	WE, WRES, WCK, RE, RRES, RCK, D0 – D7			-1.0	μA
Іогн	Off-state high-level output current	Vo=Vcc				5.0	μA
Iozl	Off-state low-level output current	Vo = GND				-5.0	μA
Icc	Average supply current during operation	VI = Vcc, GND, output open twck, trck = 20ns				150	mA
С	Input capacitance	f = 1MHz				10	pF
Co	Off-time output capacitance	f = 1MHz				15	pF

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SWITCHING CHARACTERISTICS (Ta=0 - 70 °C, Vcc=5V±10%, GND=0V unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Тур.	Max.	Unit
tAC	Access time			16	ns
toн	Output hold time	3			ns
t OEN	Output enable time	3		16	ns
todis	Output disable time	3		16	ns

TIMING REQUIREMENTS (Ta=0 - 70 °C, Vcc=5V±10%, GND=0V unless otherwise noted)

Symbol	Parameter		Limits		
		Min.	Тур.	Max.	Unit
twcĸ	Write clock (WCK) cycle	20			ns
twcкн	Write clock (WCK) "H" pulse width	8			ns
t WCKL	Write clock (WCK) "L" pulse width	8			ns
t RCK	Read clock (RCK) cycle	20			ns
t RCKH	Read clock (RCK) "H" pulse width	8			ns
t RCKL	Read clock (RCK) "L" pulse width	8			ns
tDS	Input data set up time for WCK	4			ns
tDH	Input data hold time for WCK	3			ns
tress	Reset set up time for WCK/RCK	4			ns
tresh	Reset hold time for WCK/RCK	3			ns
t NRESS	Reset non-selection set up time for WCK/RCK	4			ns
t NRESH	Reset non-selection hold time for WCK/RCK	3			ns
twes	WE set up time for WCK	4			ns
twen	WE hold time for WCK	3			ns
t NWES	WE non-selection set up time for WCK	4			ns
t NWEH	WE non-selection hold time for WCK	3			ns
tres	RE set up time for RCK	4			ns
treh	RE hold time for RCK	3			ns
t NRES	RE non-selection set up time for RCK	4			ns
t NREH	RE non-selection hold time for RCK	3			ns
tr, tf	Input pulse up/down time			20	ns
tн	Data hold time (Note 1)			20	ms

Note 1: For 1 line access, the following conditions must be satisfied:

 $\overline{\text{WE}}$ high-level period $\leq 20 \text{ ms} - 8192 \cdot \text{tWCK} - \overline{\text{WRES}}$ low-level period

 $\overline{\text{RE}}$ high-level period $\leq 20 \text{ ms} - 8192 \cdot \text{tRCK} - \overline{\text{RRES}}$ low-level period

2: Perform reset operation after turning on power supply.

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tODIS and tOEN measurement condition



OPERATION TIMING

• Write cycle



• Write reset cycle



WE = "L"

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• Matters that needs attetion when WCK stops

Input data of n cycle is read at the rising edge after WCK of n cycle and writing operation starts in the WCK low-level period of n+1 cycle. The writing operation is complete at the falling edge after n+1 cycle.

To stop reading write data at n cycle, enter WCK before the rising edge after n+1 cycle.

When the cycle next to n cycle is a disable cycle, WCK for a cycle requires to be entered after the disable cycle as well.

Read cycle



• Read reset cycle



MITSUBISHI <DIGITAL ASSP> M66258FP

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VARIABLE LENGTH DELAY BIT

• 1 line (8192 bits) delay

Input data can be written at the rising edge of WCK after write cycle and output data is read at the rising edge of RCK before read cycle to easily make 1 line delay.



• n-bit delay bit

(Reset at cycles according to the delay length)



• n-bit delay 2

(Slides input timings of $\overline{\mathsf{WRES}}$ and $\overline{\mathsf{RRES}}$ at cycles according to the delay length.)



• n-bit delay 3

(Slides address by disabling $\overline{\mathsf{RE}}$ in the period according to the delay length.)



• Reading shortest n-cycle write data "n"

(Reading side n-1 cycle starts after the end of writing side n-1 cycle.)

When the reading side n-1 cycle starts before the end of the writing side n+1 cycle, output Qn of n cycle is made invalid. In the following diagram, reading operation of n-1 cycle is invalid.



• Reading longest n-cycle write data "n": 1 line delay

(When writing side n-cycle <2>* starts, reading side n cycle <1>* then starts.)

Output Qn of n cycle <1>* can be read until the start of reading side n cycle <1> and the start of writing side n cycle <2>* overlap each other.



<0>*, <1>* and <2>* indicate value of lines.

APPLICATION EXAMPLE



Sub Scan Resolution Compensation Circuit with Laplacean Filter